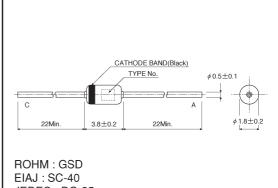
High-speed switching diode 1N4148 / 1N4150 / 1N4448 / 1N914B

*This product is available only outside of Japan.

JEDEC Standard Product

The following 1N series diodes are available to support the JEDEC standard.

External dimensions (Units: mm)



JEDEC: DO-35

● Absolute maximum ratings (Ta = 25°C)

Туре	V _{ВМ} (V)	V _R (V)	I _{FM} (mA)	lo (mA)	I _F (mA)	I _{FSM} 1 μs (A)	P (mW)	Tj (℃)	Topr (°C)	Tstg (℃)
1N4148	100	75	450	150	200	2	500	200	−65~+200	-65~+200
1N4150	50	50	600	200	250	4	500	200	−65~+200	−65∼+200
1N4448	100	75	450	150	200	2	500	200	−65~+200	−65∼+200

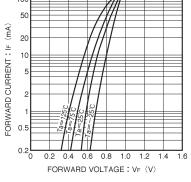
• Electrical characteristics (Ta = 25°C)

		VF (V)											BV (V) Min.		IR (μA) Max.				Cr (pF)	trr (ns)
Туре	@ 0.1mA	@ 0.25mA	@ 1mA	@ 2mA	@ 5mA	@ 10mA	@ 20mA	@ 30mA	@ 50mA	@ 100mA	@ 200mA	@ 250mA	@ 5μA	@ 100 μ A	@2	5℃ Vn(V)		50°C VR (V)	V _R =0 f=1MHz	V _R =6V I _F =10mA R _L =100Ω
1N4148						1/						75	100	0.025	20	50.0	20		4	
						1.0							/5	100	5.0	75	30.0	20	_ +	
1N4150			0.54 0.62			0.66			0.76		0.87		_	50	0.1	50	100.0	50	2.5	4
1N4448 (IN914B)			$\overline{/}$		0.62 /					1.0			_	100	0.025 5.0	20 75	50.0	20	4	4

The upper figure is the minimum VF and the lower figure is the maximum VF value.

REVERSE RECOVERY TIME: trr (ns)





3 000 æ 1.000 REVERSE CURRENT: IR 300 REVERSE VOLTAGE: VR (V)

3.0 (Jd) f=1MHz CAPACITANCE BETWEEN TERMINALS: CT 2.0 1.5 1.0 0.5 0 r 10 15 20 25 REVERSE VOLTAGE: VR (V)

Fig. 3 Capacitance between

terminals characteristics

Fig. 1 Forward characteristics

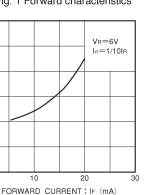


Fig. 2 Reverse characteristics

100 PULSE 3 50 Single pulse SURGE CURRENT: Isurge 20 10 0.1 100 1 000 10 000 PULSE WIDTH: Tw (ms)

Fig. 4 Reverse recovery time characteristics

20

Fig. 5 Surge current characteristics

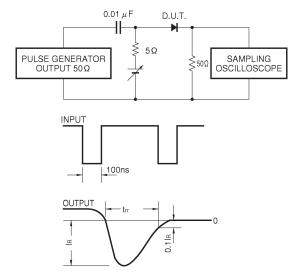


Fig. 6 Reverse recovery time (trr) measurement circuit